

SUBJECT INDEX

A

- Acceptors
 - in lead zirconate-titanate ceramic, 40
- Adhesion
 - and ion bombardment, 356-57
 - β/β'' -alumina
 - hydration, 282
 - proton transport in the, 279-94
 - structure, 280-81
- Aluminum
 - Al islands, 75, 76-77
 - Al particles
 - in high magnetic field, 57
 - high-speed machining of, 232, 234-36, 239, 240, 276
 - studied for superconductivity 63-65
 - interface
 - and a $Hg_{1-x}Cd_xTe$ substrate, 89
- Ammonium β -alumina, 282-84
- Ammonium/hydronium β'' -alumina, 290-92
- Amorphous-semiconductor substrates, 87-89
- Antennas
 - ultrasonic, 45-46

B

- Band-mapping technique
 - for semiconductors, 70-71
- Band theory
 - of metallic particles, 50
- Barium
 - $BaTiO_3$
 - coercive field of, 46
 - (Ba, Ca)/ TiO_3 , 32
 - (Ba, Pb)/ TiO_3 , 32
 - barium titanate, 33
 - and derived piezoelectric mixed-crystal ceramics 28-32
- BCS theory, 62
- Boltzmann constant, 4
- Boron-nitrogen polymers, 314
- Brittle fracture
 - theories of, 374-78
- Bulk salt position, 56-57

C

- Cadmium compounds
 - as semiconductors, 112-13
- Carbon
 - structural properties for, 130
- Carbonates
 - in ferroelectric ceramics, 43
- Carborane-siloxane polymers, 314-15
- Carrier injection
 - hot, 103
- Carrier inversion, 103, 110, 111
- Carriers
 - majority, 98, 99-100
 - minority, 98-99
- Ceramic(s)
 - brittle fracture and toughening mechanisms in, 373-401
 - complex, 41-42, 45
 - fibrous toughening in, 393-94
 - microstructural effects in, 385-99
 - piezoelectric, 27-46
 - processing, 43-44
 - from pyrolysis
 - applications, 330-32
 - forms, densities, microstructures, and properties of, 318-30
 - via polymer pyrolysis, 297-332
- CH_3CN
 - and semiconductors, 109-13
- CH_3CN solvent
 - Si in, 106-8
- Charge density
 - electronic
 - calculation of, 125-26
 - plots
 - and the pseudopotential, 127
- Charge patterns
 - in ceramics, 40-41
- Chemical properties
 - of metals modified by ion implantation, 357-62
- Chip formation
 - in high-speed machining, 237-38, 243-53, 276
- Chip thickness ratios
 - and shear angles in high-speed machining, 257-61

Cobalt

- and the local moment limit, 20-22
- Coercive field
 - in barium titanate, 29, 46
 - in lead titanate, 32, 35
 - in lead zirconate-titanate ceramic material, 34, 39
 - in piezoelectric ceramics, 31-32
- Coherent potential approximation (CPA), 13, 15
- Color
 - metallic colloids exhibit, 59
- Complex impedance measurements, 104
- Conductivity
 - of protonic forms, 220-22
 - of salt forms, 222-23
- Constant initial state, 70
- Cooper minimum method, 71, 80-81
- Cooper pair(s), 49, 64
- Copper
 - Cu particles
 - and the Knight shift, 56-57
- Corrosion
 - of metals modified by ion implantation, 359-62
- Coupling factors
 - in barium titanate crystals, 31
 - in lead titanate, 36
- Crack growth behavior, 176-78
- Crack layer propagation theory, 200-1
- Crack tip
 - craze, 196-99
 - deflection, 390-91
 - forces, 379-80
 - modeling, 196-201
 - crack layer propagation theory, 200-1
 - two-stage line zone model, 199-200
 - shielding, 391-93
 - structure, 380-85
- Cracks
 - discontinuous crack growth, 175, 176, 178, 181-87
 - fatigue, 173-81, 196-201
 - craze-shear correlation, 195
 - crazing vs shearing in, 187-96

- epsilon-shear transition, 195-96
- temperature and stress dependency, 191-92
- through-thickness cracks, 192-94
- polymer short, 174-76
- Craze
 - crack tip, 196-99
- Craze growth kinetics, 184-87
- Crazing
 - vs shearing in fatigue cracks, 187-96
- Crystallinity
 - degree of determining, 213-16
- Crystals
 - barium titanate, 28-32
 - and piezoelectricity, 27
- Curie-Weiss law, 2, 3, 9, 14, 28
- Curie-Weiss magnetic susceptibility, 1, 2
 - see also CW susceptibility
- Curie's law, 54
- Cutting forces
 - in high-speed machining, 237, 238, 255-57, 276
- Cutting speed
 - in high-speed machining, 232-40, 255-57, 276
- CW law
 - see Curie-Weiss law
- CW susceptibility, 2, 3
 - see also Curie-Weiss magnetic susceptibility
- Cyclic voltammetry, 105, 106
- D
- d bands, 6
- d electrons
 - in transition metals, 1
- d metals, 5-8
- d shell(s), 7, 20-21
- DCG
 - see Discontinuous crack growth
- Deposition processes
 - and ion implantation, 364-65
- Diamagnetic susceptibility, 61
 - of Sn particles, 62
- Dimethylformamide
 - n-type GaAs studied in, 109
- Discontinuous crack growth, 175, 176, 178, 181-87
 - and craze growth kinetics, 184-87
 - history, 182-84
- Donors
 - in lead zirconate-titanate ceramic, 38-40
- E
- Eigenfunctions, 53
- Eigenstates, 52
- Eigenvalues, 52, 58
- Electrical properties
 - of metal modified by ion implantation, 362-64
- Electrocatalysis, 161-62
- Electrochemical properties
 - of inorganic ion exchangers, 220-25
- Electrochemical reactions
 - formal potentials, 156-57
 - kinetic aspects of voltametric waveshapes, 158-61
 - and polymer films, 156-61
 - thermodynamic aspects of voltametric waveshapes, 157-58
- Electrodes
 - bilayer, 163
 - polymer modification of, 145-65
 - polymer-modified
 - how to make, 146-56
 - sandwich, 163-64
 - spatially modified, 163-65
- Electroluminescence, 105
- Electrolytes
 - in solar cell systems, 95
- Electron
 - the one-electron theory of metallic particles, 50
 - itinerant electron magnetism, 1-23
 - see also Electrons
- Electron-hole pairs, 97-98
- Electron spin resonance, 58
 - conduction, 63
- Electronic properties
 - of small particles, 49-65
- Electronic specific heat
 - of small particles, 51-53
- Electrons
 - conduction, 55
 - the quantum states of, 58
 - core
 - in Si, 119-20
 - d electrons, 1
 - odd, 58
 - in a small particle, 53, 54
 - the wave function of, 65
 - valence
 - in a crystalline material, 50
 - in Si, 119-20
 - see also Electron
- Elliott formula, 55
- Elliott mechanism, 58
- Elliott theory, 57
- Empirical pseudopotential method, 121
 - see also Pseudopotential
- Energy distribution curves (EDC)
 - photoelectron, 68
 - for the Si(111)-Pd interface, 81
 - valence-band
 - for Sm on Si, 79-80
 - valence-electron, 80
- EPM
 - see Empirical pseudopotential method
- Epsilon plastic zone, 174-76
- F
- Fatigue
 - in bulk materials
 - modified by ion implantation, 355-56
 - polymer, 171-202
 - and the short crack problem, 173-81
- Fermi, E.
 - the work of, 119
- Fermi distribution function, 51
- Fermi level
 - pinning, 101, 103, 107, 113, 115
 - in CH_3CN solvent, 107
 - in semiconductors, 69, 73-75, 78, 82, 96, 100
 - shift, 71-72
- Fermi liquid theory
 - of metallic particles, 50
- Ferroelectric ceramics, 27, 46
 - processing, 43-44
- Ferroelectricity
 - and piezoelectricity, 28
- Ferromagnetism, 1-2, 6
- Ferromagnets
 - weak itinerant, 8-11
- Fibrous toughening
 - in ceramics, 393-94
- Filters
 - mechanical, 41, 44
- Fluctuation theory, 63
 - microscopic, 62
 - for orbital diamagnetism, 61
- Foil technique
 - in ceramics, 44

- Friction
 - of metal modified by ion im-
plantation, 348-50
- G
- Gallium.
 - GaAs
 - Al islands on, 76-78
 - p-type, 109
 - n-GaAs
 - in CH_3CN solvent, 108-9
 - and the pseudopotential,
126
 - GaAs-Al system, 75
 - Schottky barrier formation
for the, 72
 - n-GaP
 - as a semiconductor, 109-10
- Germanium
 - amorphous, 87-89
 - crystalline, 88
 - Schottky barrier formation on,
78-82
 - structural properties for, 130
- Grüneisen parameters
for silicon, 132
- H
- Hamiltonians
 - orthogonal, 52, 57
 - symplectic, 53
 - unitary, 53
- Hardeners
 - in ceramics, 46
 - in complex ceramics, 41
 - in lead zirconate-titanate ce-
ramic, 40
- Hardness
 - of metals modified by ion im-
plantation, 350
- Hartree-Fock approximation
(HFA) 1, 2, 13
- Heat
 - electronic specific
of small particles, 51-53
- Heisenberg model 1-2, 4, 5, 8,
13, 21
- Heterojunction devices, 83
- Heterojunction interfaces, 68,
69, 82-87
- research on, 90
- the valence-band discon-
tinuities at, 67
- HF-RPA theory
of itinerant electron magne-
tism, 2, 3
- HFA
see Hartree-Fock approxima-
tion
- High-speed machining
 - analytical models, 253-55,
276
 - applications, 266-75
 - chip formation, 237-38, 243-
53, 276
 - cutting forces, 237, 238, 255-
57, 276
 - cutting speed, 232-40, 255-
57, 276
 - early work, 232-40
 - facilities, 240-43
 - of metals, 231-77
 - shear angles and chip thick-
ness ratios, 257-61, 276
 - surface finish, 238-40, 276
 - tool wear, 234-36, 261-66,
276-77
 - and tools, 232-42
- Hot carrier injection
in the semiconductor/liquid in-
terface, 103
- Hydration
of B/B^{III} -alumina compounds,
282
- Hydrogen
 - implanted into metals, 368
- Hydrogen B -alumina, 284-85
- Hydronium B -alumina, 285-87
- Hydronium B^{III} -alumina, 288-90
- I
- Indium
 - InP
 - as a semiconductor, 109
 - p-type InP
 - as a semiconductor, 110
- Insulators
 - the empirical pseudopotential
method for, 124-33
- Interface behavior
characteristic of surface states,
101
- Interfaces
 - the application of pseudo-
potentials to, 124
- heterojunction, 82-87
- ideal, 96-101
- and the pseudopotential, 136-
42
- semiconductor/liquid
photoeffects at the, 95-115
- semiconductor
synchrotron radiation photo-
emission spectroscopy
of, 67-91
- Internal field
 - in ceramics, 40
 - in complex ceramics, 42
- Ion conductors
 - fast, 218-19
- Ion exchange
 - in fused salt, 219-20
- Ion exchange polymer films,
150-52
- Ion exchange properties, 209-13
- Ion exchangers
 - catalytic properties of, 223-25
 - dehydrated, high temperature,
and triphosphate phases
of, 126-18
 - determination of degree of
crystallinity of, 213-16
 - electrochemical properties of,
220-25
 - inorganic
 - with layered structures,
205-27
 - preparation of, 206-8
- Ion gates, 165
- Ion implantation
 - and chemical properties
modification, 357-62
 - and deposition processes,
364-65
 - and electrical and
optical properties modifica-
tion, 362-64
 - for investigating phase trans-
formations, 366-67
 - materials modification by,
342-65
 - and materials research, 365-
68
 - and mechanical properties
modification, 344-57
 - in metals, 335-68
 - physics of, 336-42
 - and radiation effects, 367-68
- Iron
 - and the local moment limit,
20-22
- Iron oxide
 - as a stabilizer in ceramics, 46
- K
- Knight shift, 55-56, 57, 63
for Sn particles, 63
- Knitline crack, 193-94
- Knitlines
 - in polymers, 192
- Kramers doublet(s), 53, 58
- L
- Langevin-Weiss mechanism, 2
- Lanthanum
 - piezoelectric ceramic doped
with, 40
- Layered compounds, 110-12
- organic derivatives of the, 226

- α -Layered compounds
 - structure of, 208
- γ -Layered compounds, 225-26
- Layered structure(s)
 - inorganic ion exchangers with, 205-27
- α -Layered structure(s), 206-25
- Lead
 - Pb(Zr, Ti)O₃ in the tetragonal phase, 35-36
 - Pb(Zr,Ti_{1-x})O₃ tetragonal, 36
 - Pb(ZrTi)O₃ and piezoelectric ceramics, 46
- Lead oxide(s), 33-34
- Lead titanate-lead zirconate rhombohedral, 36-37
- Lead zirconate-titanate ceramic(s), 28, 44
 - tetragonal, 44
 - tetragonal to rhombohedral phase transition of, 37
- Lead zirconate-titanate system in piezoelectric ceramics, 32-42
- LEFM
 - see Linear elastic fracture mechanics
- Light
 - plasma oscillation absorption of, 59
- Light intensity
 - and open circuit photovoltage in semiconductors, 104
- Linear elastic fracture mechanics (LEFM), 173
 - the breakdown of, 179-81
- Lithium
 - Li particles
 - Knight shift of, 55-56
 - sharp absorption lines in particles of, 59
- Local moment limit, 22
- Local moment picture
 - and ferromagnetism, 1-2
 - and itinerant electron magnetism, 2-3
- Local moment theory of magnetism, 4-8
- M
- Machining
 - high-speed
 - of metals, 231-77
- Magnesium
 - in complex ceramics, 42
- Magnetic field
 - and superconductivity in small particles, 64
- Magnetic properties
 - of small particles, 54-59
- Magnetic susceptibility
 - of small particles, 54
- Magnetism
 - itinerant electron, 1-23
- Manganese
 - as a stabilizer in complex ceramics, 42
- Manganese oxide
 - as a stabilizer in ceramics, 41
- Materials research
 - and ion implantation, 342-65
- Materials research
 - and ion implantation, 365-68
- Mechanical properties
 - of surfaces modified by ion implantation, 344-57
- Medical electronics
 - lead titanate ceramic for, 35
- Medical engineering
 - ultrasonic transducers for, 45-46
- Metal
 - friction of
 - and ion implantation, 348-50
 - see also Metals
- Metal oxides, 113-14
- Metal chalcogenides, 110-12
- Metallic colloids
 - exhibit color, 59
- Metallic particle
 - the electrical neutrality of a, 50-51
- Metallurgical parameters
 - and ion implantation, 365-66
- Metals
 - chemical properties of
 - modified by ion implantation, 357-62
 - d metals, 5-8
 - free electron model of, 49-50
 - hardness of
 - and implantation, 350
 - high-speed machining of, 231-77
 - ion implantation in, 335-68
 - magnetism of, 18-22
 - and the pseudopotential approximation, 133-36
 - the quantum theory of, 49-50
 - and the short crack problem, 173-74
 - transition
 - d electrons in, 1
 - ferromagnetic, 2
 - weakly ferro- and antiferromagnetic, 3
 - weakly ferromagnetic, 3, 8-11, 13-15
 - wear mechanisms in, 350-54
 - wear of
 - and ion implantation, 344-48
- Microphone
 - piezoelectric, 44
- Microstructural effects
 - in ceramics, 385-99
 - crack growth resistance, 390-99
 - size effects, 386-89
- Microstructure
 - and the short crack anomaly, 179
- Molybdenum
 - MoS₂
 - as a semiconductor, 110-12
 - MoSe₂
 - as a semiconductor, 110-12
- Monomers
 - films formed from, 152-56
- N
- Nickel
 - and the local moment limit, 20-22
- Niobium
 - in complex ceramics, 42
 - piezoelectric ceramic doped with, 40
- NMR
 - see Nuclear magnetic resonance
- Nonporosity
 - in ceramics
 - methods ensuring, 43
- Nuclear magnetic resonance (NMR), 55
- O
- One-electron theory
 - of metallic particles, 50
- One-particle theory
 - of small particles, 51
- Optical resonance absorption
 - of small particles, 59-60
- Organosilane condensation, 153
- Orthogonal ensemble
 - of Hamiltonians, 52
- see also Hamiltonians
- Orthogonalized plane wave (OPW), 119
- Oxidation
 - of metals modified by ion implantation, 357-59
- Oxides
 - added to lead zirconate-titanate ceramic, 38
 - in ferroelectric ceramics, 43
- P
- Pair breaking
 - diamagnetic, 64
 - paramagnetic, 64-65

- Particle(s)
 even, 57
 odd, 57
 small
 electronic properties of, 49-65
 electronic specific heat of, 51-53
 magnetic properties of, 54-59
 research, 142
 superconductivity of, 60-65
 wave function of electrons in a, 65
- Particulates
 polymer films with, 164-65
- Permittivity
 in lead zirconate-titanate ceramic material, 39
 in the lead zirconate-titanate system, 32
 of $\text{Pb}(\text{Zr,Ti})\text{O}_3$, 35-36, 37, 46
 in piezoelectric ceramics, 32
- Perovskite group
 ferroelectrics of the, 27
- Perovskite-type systems
 ferroelectric and piezoelectric, 28-35
- Photocurrent-voltage response
 as a measurement technique, 103-4
- Photoeffects
 the semiconductor/liquid interface, 95-115
- Photoelectrochemical reactions, 162-63
- "Photoelectron diffraction," 71
- Photoelectrons, 70
- Photoemission
 synchrotron radiation, 67-91
- Photoionization cross section, 71
- Photoluminescence, 105
- Photon frequencies
 for silicon, 132
- Photons
 polarized, 70
- Photovoltage
 open circuit, 104
- Piezoelectric ceramics, 27-46
 and barium titanate, 28-32
 and lead-zirconate-titanate, 32-42
- Piezoelectric microphone, 44
- Piezoelectricity, 27
 and ferroelectricity, 28
- Plasma oscillation
 absorption of light by, 59
- Plasma polymerization, 153-56
- Platinum particles
 electronic specific heat in, 53
- Polarization
 in barium titanate, 29-30, 46
 in ceramics, 40
 in lead titanate, 32, 36
 in lead zirconate, 33
 in the lead zirconate-titanate system, 34
 photon, 70
 in piezoelectric ceramics, 31-32
 and transducers, 42-43
- Polymer
 precursor chemistry, 298-318
 see also Polymers
- Polymer fatigue, 171-202
- Polymer films
 ion exchange, 150-52
 with particulates, 164-65
 redox, 147-50
- Polymer modification
 of electrodes, 145-65
- Polymer pyrolysis
 ceramics via, 297-332
- Polymer short cracks, 174-76
- Polymerization
 electrochemical, 152-53
 plasma, 153-56
- Polymers
 boron, 314-15
 SiC preceramic, 301-9
 silicon-nitrogen, 309-14
 see also Polymer
- Propylene carbonate (PC)
 n-type GaAs studied in, 109
- Proton transport
 in the B'B''-aluminas, 279-94
- Protonic beta-aluminas, 282-87, 292-94
- Protonic B''-aluminas, 288-94
- Protonic forms
 conductivity of, 220-22
- Pseudopotential
 applied to solids, 119-43
- Pyrolysis
 mechanisms and yields, 315-18
- Q**
 q space, 3, 8-11, 20-22
 Quantum size effects, 59
 Quantum theory
 of metals, 49-50
 Quartz crystals, 27
- R**
 Radiation
 synchrotron photoemission spectroscopy with, 67-91
- Radiation effects
 using high-energy ion beams, 367-68
- Random matrix theory
 of small particles, 52
- Random phase approximation, 2
- Rare earth(s)
 experiments on, 79
 photoemission experiments performed on, 78
- Recombination
 diffusion-recombination in semiconductors, 100
 in semiconductors, 103-5
- Recombination pathways
 in semiconductors, 101
- Redox polymer films
 using preformed polymers, 147-50
- Redox potential
 and barrier height, 99
 and V_{ec} , 99-101
- Reflectivity
 of ion-implanted metals, 364
- Relaxation
 in bulk normal metals and small particles, 57
 nuclear spin-lattice, 61
 processes, 49
 spin
 of conduction electrons, 55
- Relaxation time, 60
 nuclear spin-lattice, 57-58
- Resonant photoemission method, 71
- Resonators
 acoustic cavity, 44
 stabilized ceramic used for, 41
 thickness, 45
- S**
 Salt
 rochelle, 27
- Salt electrodes
 molten
 n-type GaAs studied in, 109
- Salt forms
 conductivity of, 222-23
- Salts
 acid
 with fibrous structure, 226
 with three-dimensional structure, 226-27
 with unknown structure, 227
 anhydrous, 219-20
 fused, 219-20
 Schottky barrier, 67, 68
 Schottky barrier formation
 on silicon and germanium, 78-82
 on III-V compounds, 71-78
 Schottky barrier height, 82
 Schottky barrier theory, 100
 SCR theory
 see Self-consistent renormalization theory

- Self-consistent renormalization, 15
- Self-consistent renormalization theory (SCR), 8, 11, 19, 22 of spin fluctuations, 3
- Semiconductor interfaces and heterojunction interfaces, 82-87, 90 and the Schottky barrier, 71-82
- Semiconductor/liquid interface behavior under illumination, 97-99 dark behavior, 96-97 hot carrier injection, 103 ideal interfaces, 96-101 measurement techniques, 103-6 photoeffects at the, 95-115 surface states, 101-3
- Semiconductor surfaces synchrotron radiation photoemission spectroscopy of, 67-91
- Semiconductor systems in nonaqueous solvents, 106-14
- Semiconductors the empirical pseudopotential method for, 124-33 optical properties of the empirical pseudopotential method approach for, 133
- Shear angles and chip thickness ratios in high-speed machining, 257-61
- Shearing vs crazing in fatigue cracks, 187-96
- Shell(s) d shell(s), 7, 20-21
- Silicon amorphous, 87-89 amorphous hydrogenated, 114 core and valence electrons in, 119-20 crystalline, 88 Grüneisen parameters for, 132 in nonaqueous electrolytes, 106-8 p-type Si in CH_3CN , 107-8 photon frequencies for, 132 and the pseudopotential, 126-27, 129 Schottky barrier formation on, 78-82 SiC preceramic polymers, 301-9 structural properties for, 130 Silicon-nitrogen polymers, 309-14
- Sodium sharp absorption lines in particles of, 59
- Softeners in ceramics, 46 in complex ceramics, 41 in lead zirconate-titanate ceramic, 38-40
- Solar cell systems, 95
- Solar energy, 95
- Solids the pseudopotential applied to, 119-43
- Space q -space, 3, 8-11, 20-22 reciprocal, 2, 3, 8-11, 22
- Spectroscopy photoemission of semiconductor surfaces and interfaces, 67-91
- Spicer's defect model, 67, 72-73
- Spin density fluctuations, 2, 13, 22
- Spin fluctuations, 12-13, 14, 18, 22, 23 and itinerant electron magnetism, 3-5, 8 in the local moment system, 8 in weakly ferromagnetic metals, 8, 10-11
- Spin-orbit coupling, 52, 53, 58 of small particles, 54-55
- Spin-orbit interaction, 55
- Spin-orbit scattering, 63, 64
- Spin susceptibility of conduction electrons, 55 of even particles, 57 of odd particles, 57 of superconducting particles, 63
- Spin waves, 19 sloppy, 21
- Stabilizer(s) in ceramics, 40, 46 in complex ceramics, 42 iron oxide as a, 46 in tetragonal lead zirconate-titanate, 44
- Stiffness constant(s), 14, 15, 21
- Stoner theory, 1, 2, 3
- Superconductivity and ion implantation, 362-64 of small particles, 60-65
- Superexchange the Anderson, 4, 6
- Surface states in semiconductor/liquid interfaces, 101-3
- Surfaces and the pseudopotential, 136-42
- Symplectic ensemble, 53
- T
- Telephone transmission systems mechanical filters in long-distance, 44
- Temperature Curie, 1, 4, 14 in barium titanate, 32 in ceramics, 40 of lead titanate, 35
- Tetrahydrofuran (THF) n-type GaAs studied in, 109
- Thermodynamic properties of metallic particles, 50 of small particles, 53
- Through-thickness cracks, 192-94, 195
- Tin Sn particles studied for superconductivity, 63-65
- Titanium TiO_2 in semiconductor studies, 113
- Ti-O chains, 46 in barium titanate, 28, 29, 32 in $\text{Pb}(\text{Zr}, \text{Ti})\text{O}_x$, 33-34 (Ti, Zr)-O chains, 36, 42
- Titanium atoms in barium titanate, 28
- Tool ledge, 267-70
- Tool machining rotary, 270-75
- Tool wear in high-speed machining 234-36, 261-66, 276-77
- Tools and high-speed machining, 232-42 wear of, 354-55
- Toughening fibrous in ceramics, 393-94 methods of in ceramics, 396-99 transformation in ceramics, 394-96
- Transducer(s) a bending, 43 broadband sonic and ultrasonic, 40 compound, 44 high-power ultrasonic, 46 longitudinal, 42 piezoelectric, 42, 44 power, 41 sensitive acoustic or ultrasonic, 42 transversal, 42-43 ultrasonic, 45-46
- Transformation toughening in ceramics, 394-96

U

Unitary ensemble, 53

V

"Valley of Death"
in high-speed machining, 232,
233

Voltametric waveshapes
kinetic aspects of, 158-61
thermodynamic aspects of,
157-58

Voltametry
cyclic, 105, 106

W

Wave function
of electrons in a small parti-
cle, 65

Wave functions, 124, 135
atomic

determining the pseudo-
potential from, 123

Wear

of metals modified by ion im-
plantation, 344-48

tool
in high-speed machining,
261-66, 276-77

Wear mechanisms
in metals, 350-54

Z

Zirconium phosphates
and ion exchange, 206-27